



PTO/SB/08A (10-01)

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<b>Substitute for form 1449A/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/087,744
				Filing Date	March 5, 2002
				First Named Inventor	Glen Hush
				Art Unit	2811-2818
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0485/P485

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

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		Number-Kind Code <sup>2</sup> (if known)			
TL	AA	5,761,115	06/02/1998	Kozicki et al.	—
TL	AB	6,084,796	07/04/2000	Kozicki et al.	—
TL	AC	5,914,893	06/22/1999	Kozicki et al.	—
TL	AD	5,896,312	04/20/1999	Kozicki et al.	—
TL	AE	6,388,324	05/14/2002	Kozicki et al.	—
TL	AF	US 2002/0000666	01/03/2002	Kozicki et al.	—
TL	AG	5,500,532	03/19/1996	Kozicki et al.	—
TL	AH	6,418,049	07/09/2002	Kozicki et al.	—
TL	AI	5,751,012	05/12/1998	Wolstenholme et al.	—
TL	AJ	5,789,277	08/04/1998	Zahorik et al.	—
TL	AK	6,348,365	02/19/2202	Moore et al.	—
	AL				
	AM				
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	AO				

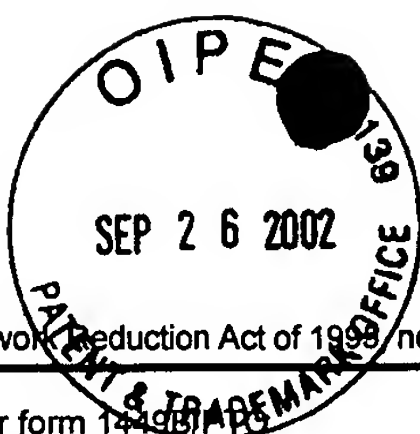
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TL	BA	WO 02/21542	03/14/2002	Kozicki et al.	—	
TL	BB	WO 00/48196	08/17/2000	Kozicki et al.	—	
TL	BC	WO 97/48032	12/18/1997	Kozicki et al.	—	
TL	BD	WO 99/28914	06/10/1999	Kozicki et al.	—	

Examiner Signature	<i>Uroyle</i>	Date Considered	5/03
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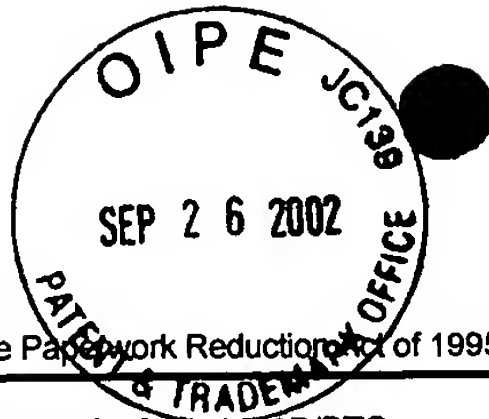
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Substitute for form 1449b <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/087,744
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				Examiner Name	Not Known
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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TL	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
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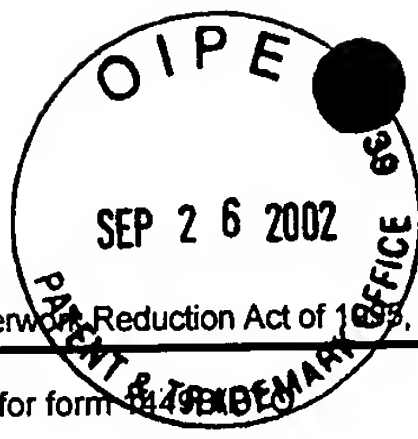


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Substitute for form 1449B/PTO				C mplet if Known	
				Application Number	10/087,744
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (use as many sheets as necessary)				Filing Date	March 5, 2002
				First Named Inventor	Glen Hush
				Group Art Unit	2811
				Examiner Name	Not Known
Sheet	3	of	8	Attorney Docket Number	M4065.0485/P485

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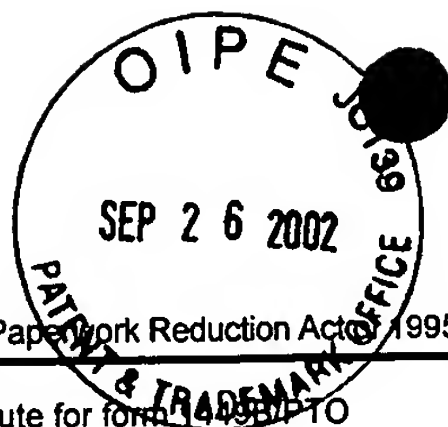
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TL		silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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TL	CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.	

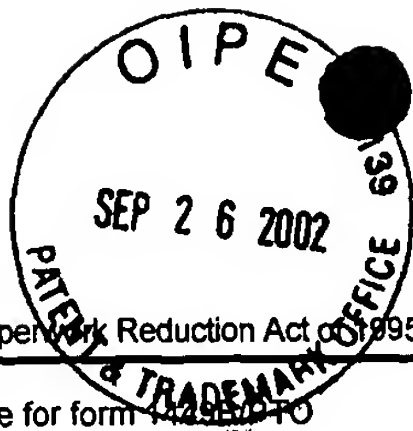


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Substitute for form PTO 10				Complete if Known	
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TL	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
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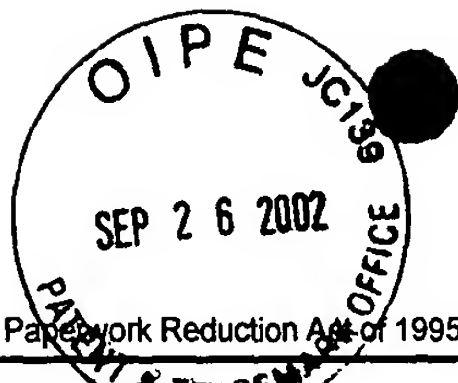
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			First Named Inventor	Glen Hush	
			Group Art Unit	2811	
			Examiner Name	Not Known	
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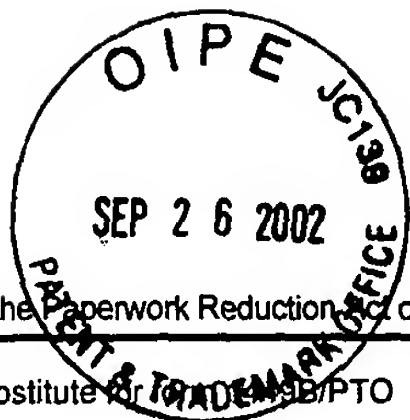
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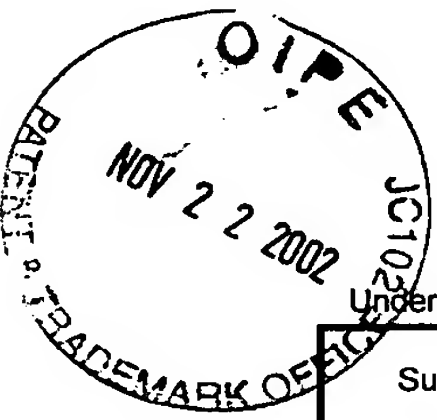
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